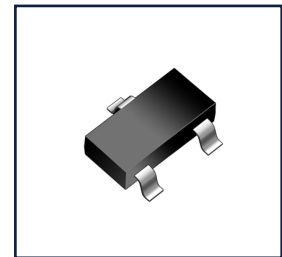


General description

These dual monolithic silicon surge protection diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment. as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Features and benefits

- 2 Unidirectional transil functions
- Reverse stand-off voltage: 5.0V Max
- Low leakage current: nA Level
- Response time is typically < 1 ns
- ESD Protection: 15kV(air)/ 8kV(contact) (IEC61000-4-2)



SOT23

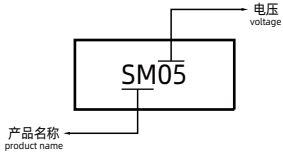
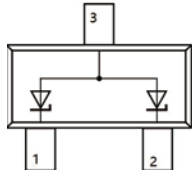
Application information

- Computers
- Printers
- Communication systems
- Cellular Handsets and Accessories
- Portable Electronics
- Industrial Controls
- Set-Top Box

Ordering information

Device	Package	Reel Size	Qty(PCS)
SM05	SOT23	7 Inch	3000

Ordering information

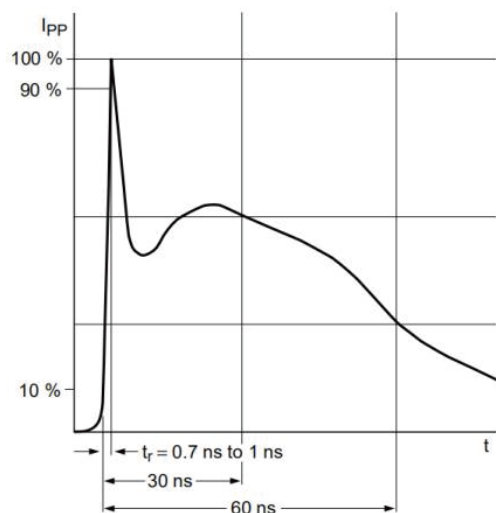
Marking	Naming rule	Graphic symbol
M05		

Maximum Ratings ($T_A = 25^\circ\text{C}$, unless otherwise specified)

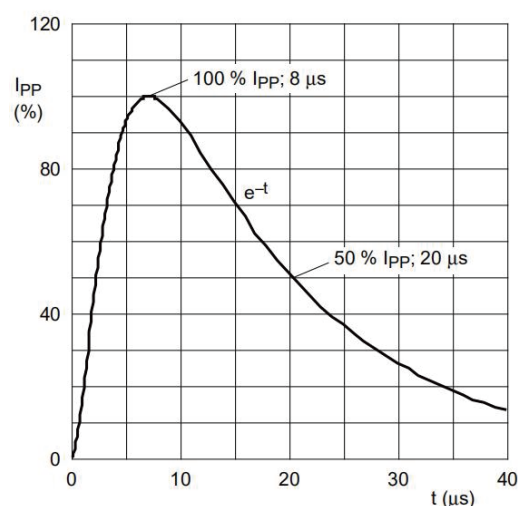
Parameter	Symbol	Value	Unit
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P_{PPM}	130	W
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PPM}	10	A
Maximum lead temperature for soldering during 10s	T_L	260	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Operating Temperature Range	T_{OP}	-40 to +125	$^\circ\text{C}$
Maximum junction temperature	T_j	150	$^\circ\text{C}$
ESD voltage IEC 61000-4-2 (air discharge)	V_{ESD}	15	kV
ESD voltage IEC 61000-4-2 (contact discharge)	V_{ESD}	8	kV

Electrical Characteristics ($T_A = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Reverse Working Voltage	V_{RWM}	--	--	5.0	V	
Breakdown Voltage	V_{BR}	6.2	--	8.0	V	$I_T=1\text{mA}$
Leakage Current I_{Leak}	I_R	--	--	100	nA	$V_{RWM}=5\text{V}$
Clamping Voltage	V_C	--	--	13.0	V	$I_{PP}=10\text{A}, T_p=8/20\mu\text{s}$
Junction Capacitance	C_j	--	60	80	pF	$V_R=0\text{V}, f=1\text{MHz}$ (Pin 1 or 2 to 3)
		--	30	40	pF	$V_R=0\text{V}, f=1\text{MHz}$ (Pin 1 to P2 and 2 to 1)

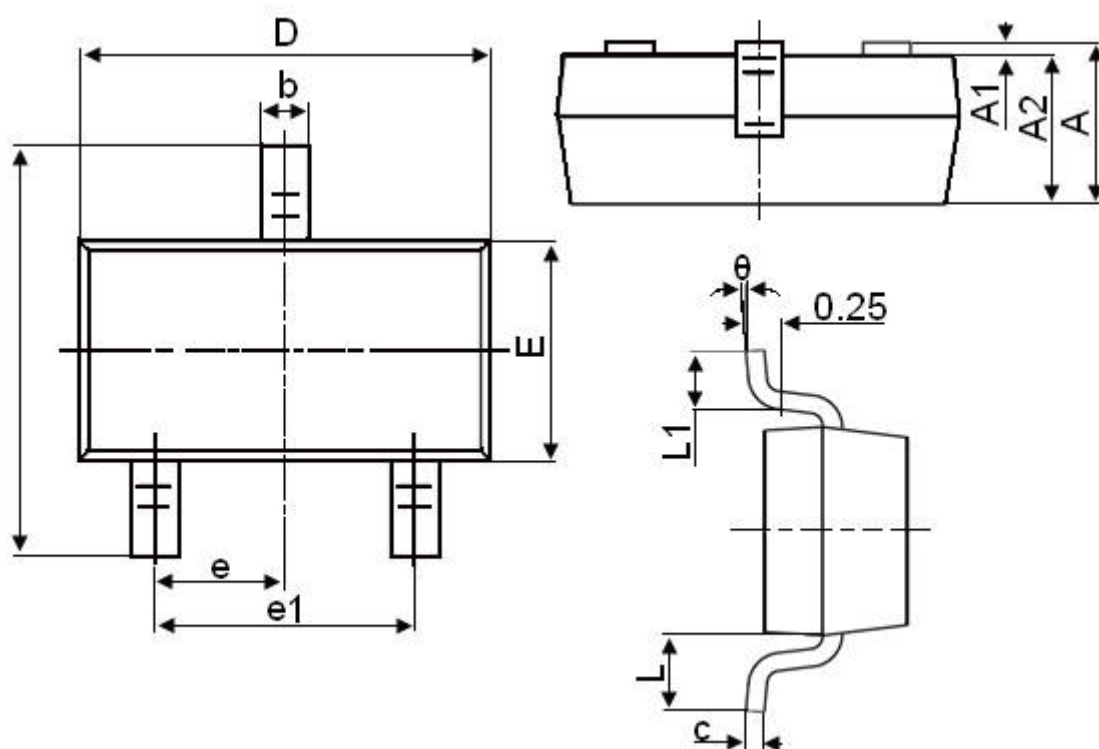


IEC61000-4-2 Waveform



IEC 61000-4-5 Waveform(8/20 μs pulse)

SOT23 Package Outline Dimensions



Symbol	Dimensions in Millimeters	
	mm	
	Min	Max
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°